

IR-Lumineszenzdiode (940 nm) mit hoher Ausgangsleistung
High Power Infrared Emitter (940 nm)
Lead (Pb) Free Product - RoHS Compliant
SFH 4233



Wesentliche Merkmale

- IR-Lichtquelle mit hohem Wirkungsgrad
- Niedriger Wärmewiderstand (Max. 9 K/W)
- Schwerpunktwellenlänge 940 nm
- ESD-sicher bis 2 kV nach JESD22-A114-E
- Erweiterte Korrosionsfestigkeit (s.a. Abschnitt Maßzeichnung)
- Die Produktqualifikation wurde basierend auf der Richtlinie AEC-Q101-REV-C, „Stress Test Qualification for Automotive Grade Discrete Semiconductors“, durchgeführt.

Features

- IR lightsource with high efficiency
- Low thermal resistance (Max. 9 K/W)
- Centroid wavelength 940 nm
- ESD safe up to 2 kV acc. to JESD22-A114-E
- Superior Corrosion Robustness (see chapter package outlines)
- The product qualification test plan is based on the guidelines of AEC-Q101-REV-C, Stress Test Qualification for Automotive Grade Discrete Semiconductors.

Anwendungen

- Infrarotbeleuchtung für Kameras
- Überwachungssysteme
- Beleuchtung für Bilderkennungssysteme

Applications

- Infrared Illumination for cameras
- Surveillance systems
- Machine vision systems

Sicherheitshinweise

Je nach Betriebsart emittieren diese Bauteile hochkonzentrierte, nicht sichtbare Infrarot-Strahlung, die gefährlich für das menschliche Auge sein kann. Produkte, die diese Bauteile enthalten, müssen gemäß den Sicherheitsrichtlinien der IEC-Normen 60825-1 und 62471 behandelt werden.

Safety Advises

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Type Type	Bestellnummer Ordering Code	Gesamtstrahlungsfluss¹⁾ ($I_F = 1A, t_p = 10ms$) Total Radiant Flux¹⁾ Φ_e (mW)
SFH 4233	Q65110A8901	≥ 320 (typ. 500)

¹⁾ gemessen mit Ulbrichtkugel / measured with integrating sphere

Grenzwerte ($T_A = 25\text{ °C}$)**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op}, T_{stg}	- 40 ... + 125	°C
Sperrschichttemperatur Junction temperature	T_J	+ 145	°C
Sperrspannung Reverse voltage	V_R	1	V
Vorwärtsgleichstrom Forward current	I_F	1	A
Stoßstrom, $t_p < 200\text{ }\mu\text{s}$, $D = 0$ Surge current	I_{FSM}	5	A
Leistungsaufnahme Power consumption	P_{tot}	1.8	W
Wärmewiderstand Sperrschicht - Lötstelle Thermal resistance junction - soldering point	R_{thJS}	9	K/W

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 1\text{ A}$, $t_p = 10\text{ ms}$	λ_{peak}	950	nm
Schwerpunktwellenlänge der Strahlung Centroid wavelength $I_F = 1\text{ A}$, $t_p = 10\text{ ms}$	$\lambda_{centroid}$	940	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 1\text{ A}$, $t_p = 10\text{ ms}$	$\Delta\lambda$	35	nm
Abstrahlwinkel Half angle	φ	± 60	Grad deg.
Aktive Chipfläche Active chip area	A	1	mm ²
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	1×1	mm ²

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics** (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, $I_F = 5\text{ A}$, $R_L = 50\text{ }\Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 5\text{ A}$, $R_L = 50\text{ }\Omega$	t_r / t_f	8 / 14	ns
Durchlassspannung Forward voltage $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$ $I_F = 5\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F V_F	1.4 (< 1.8) 2.0 (< 2.9)	V V
Strahlstärke Radiant intensity $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	I_e	170	mW/sr
Temperaturkoeffizient von I_e bzw. Φ_e Temperature coefficient of I_e or Φ_e $I_F = 1\text{ A}$, $t_p = 10\text{ ms}$	TC_I	- 0.3	%/K
Temperaturkoeffizient von V_F Temperature coefficient of V_F $I_F = 1\text{ A}$, $t_p = 10\text{ ms}$	TC_V	- 2	mV/K
Temperaturkoeffizient von λ Temperature coefficient of λ $I_F = 1\text{ A}$, $t_p = 10\text{ ms}$	$TC_{\lambda, \text{centroid}}$	+ 0.3	nm/K

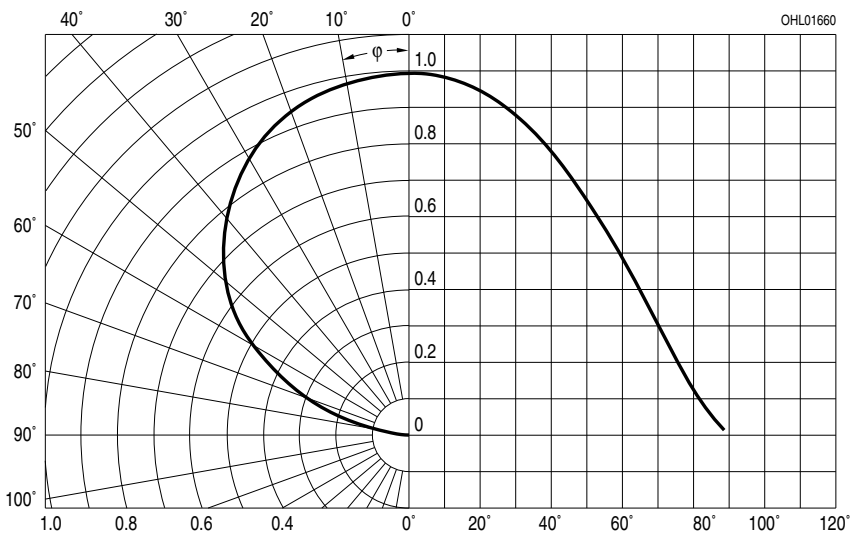
Gesamtstrahlungsfluss¹⁾ Φ_e
Total Radiant Flux¹⁾ Φ_e

Bezeichnung Parameter	Symbol	Werte Values			Einheit Unit
		-CB	-DA	-DB	
Gesamtstrahlungsfluss Total Radiant Flux $I_F = 1 \text{ A}, t_p = 10 \text{ ms}$	$\Phi_{e \text{ min}}$ $\Phi_{e \text{ max}}$	320 500	400 630	500 800	mW mW

¹⁾ Nur eine Gruppe in einer Verpackungseinheit (Streuung kleiner 1.6:1) /
Only one bin in one packing unit (variation lower 1.6:1)

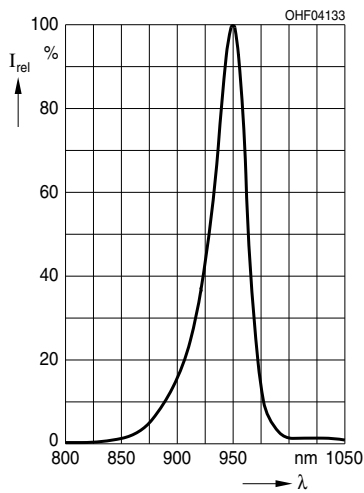
Abstrahlcharakteristik

Radiation Characteristics $I_{\text{rel}} = f(\varphi)$



Relative spektrale Emission Relative Spectral Emission

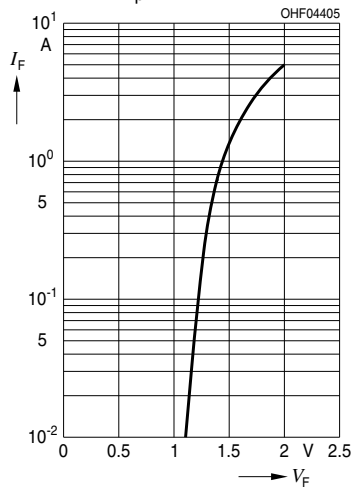
$$I_{\text{rel}} = f(\lambda)$$



Durchlassstrom Forward Current

$$I_F = f(V_F)$$

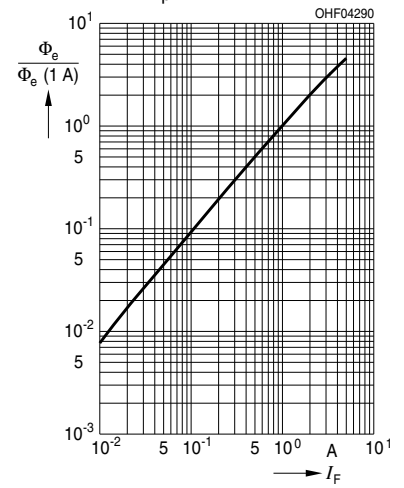
Single pulse, $t_p = 100 \mu\text{s}$



Relativer Gesamtstrahlungsfluss Relative Total Radiant Flux

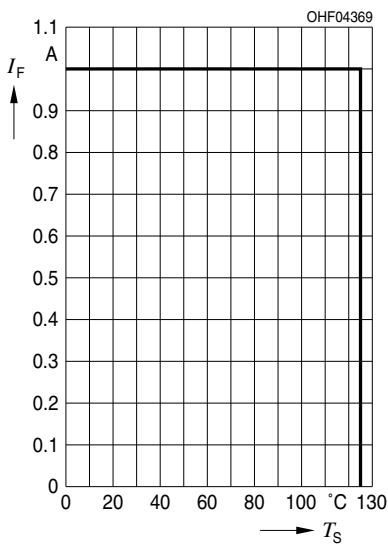
$$\Phi_e / \Phi_e(1\text{A}) = f(I_F)$$

Single pulse, $t_p = 100 \mu\text{s}$



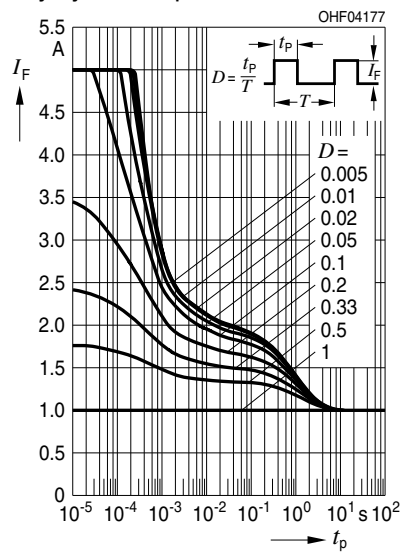
Max. zulässiger Durchlassstrom Max. Permissible Forward Current

$$I_F = f(T_A), R_{\text{thJS}} = 9 \text{ K/W}$$

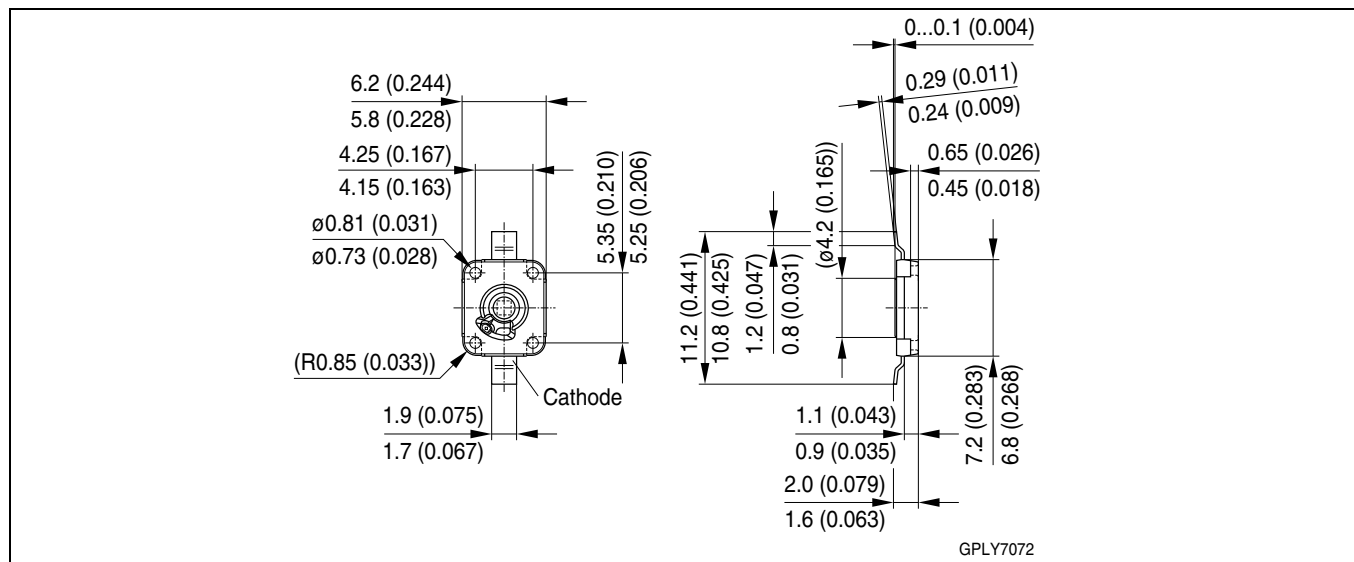


Zulässige Impulsbelastbarkeit Permissible Pulse Handling

Capability $I_F = f(t_p)$, $T_S = 85 \text{ °C}$,
Duty cycle $D = \text{parameter}$



Maßzeichnung¹⁾ Package Outlines



Korrosionsfestigkeit besser als EN 60068-2-60 (Methode 4):
mit erweitertem Korrosionstest: 40°C / 90%rh / 15ppm H₂S / 336h

Corrosion robustness better than EN 60068-2-60 (method 4):
with enhanced corrosion test: 40°C / 90%rh / 15ppm H₂S / 336h

Kathodenkennung:

Cathode mark:

Gewicht / Approx. weight:

Markierung

mark

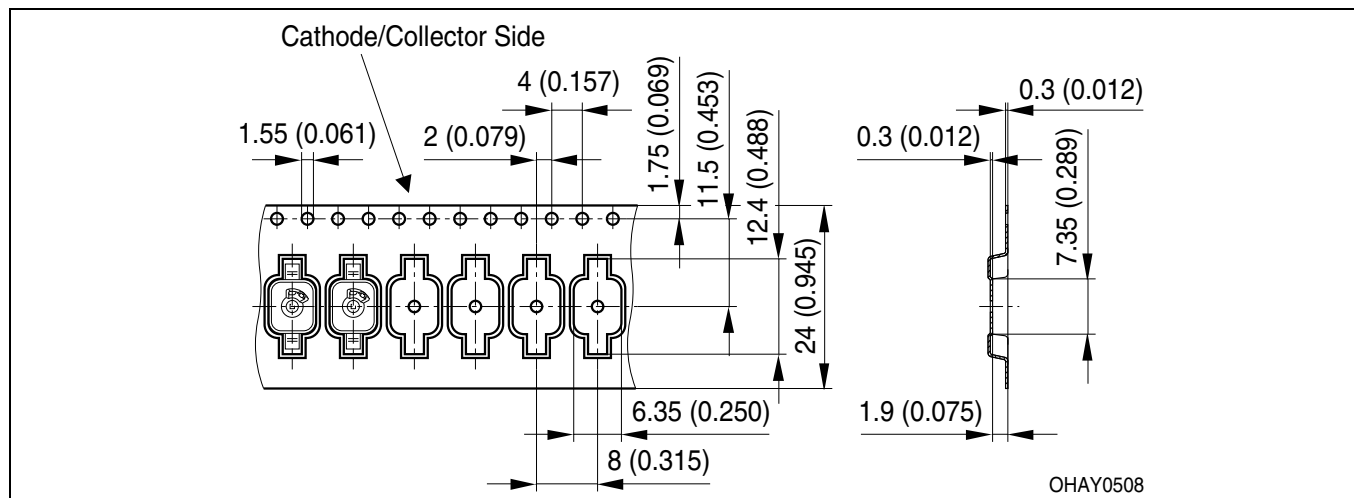
0.2 g

Gurtung / Polarität und Lage

Method of Taping / Polarity and Orientation

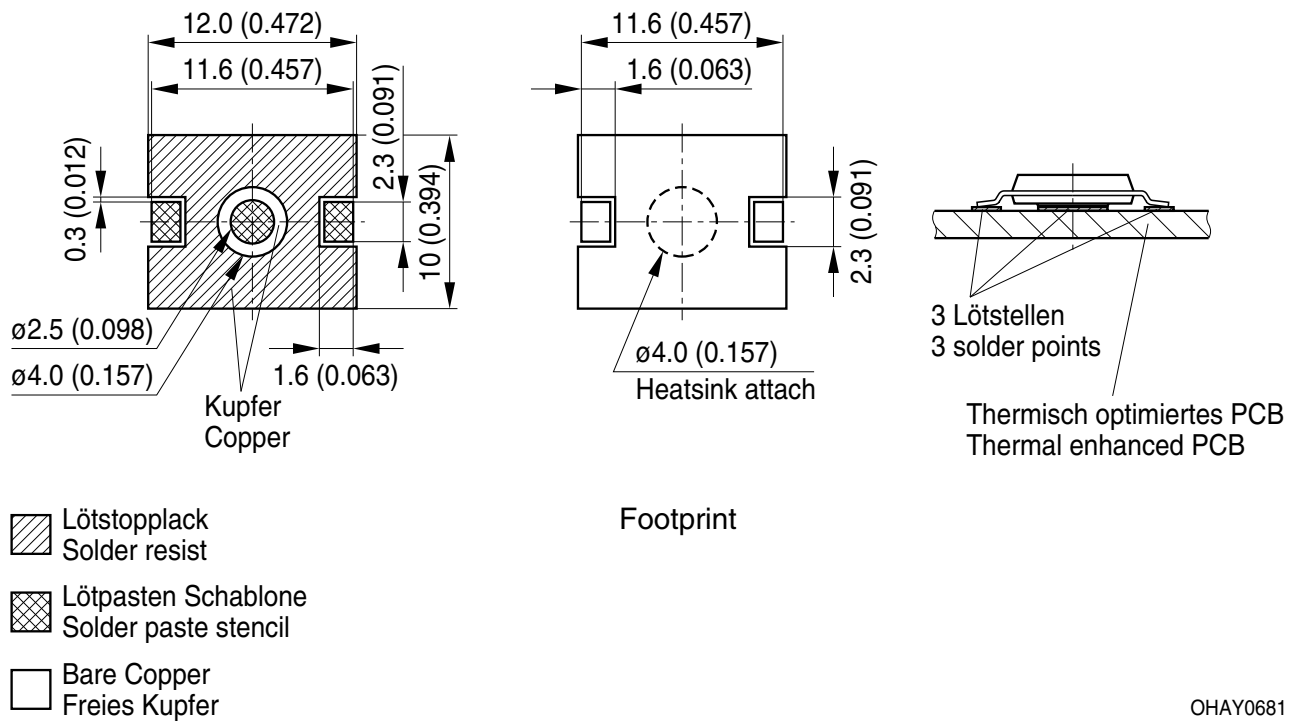
Verpackungseinheit 800/Rolle, Ø180 mm

Packing unit 800/reel, Ø180 mm



¹⁾ Maße in mm (inch) / Dimensions in mm (inch)

Empfohlenes Lötpaddesign Recommended Solder Pad Design



Achtung:

Anode und Heatsink sind elektrisch verbunden

Attention:

Anode and Heatsink are electrically connected

Lötbedingungen Soldering Conditions

Reflow Lötprofil für bleifreies Lötén

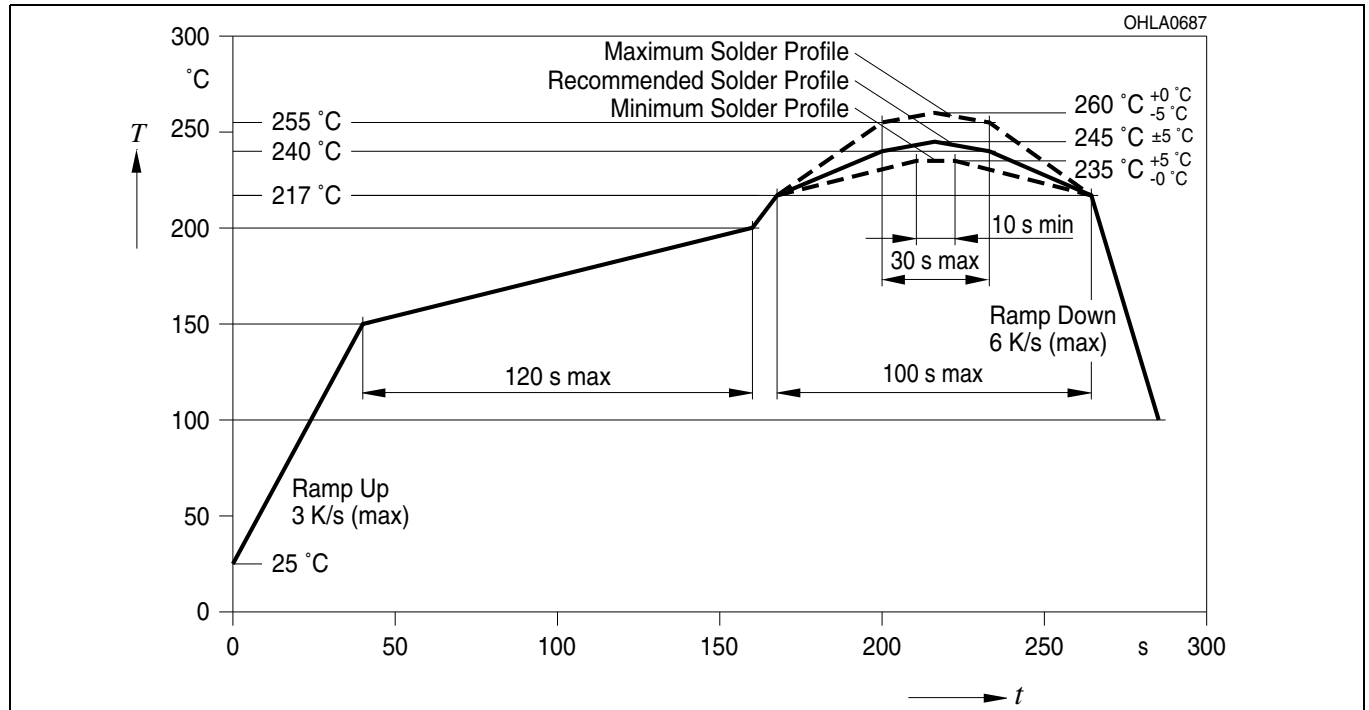
Reflow Soldering Profile for lead free soldering

Vorbehandlung nach JEDEC Level 2

Preconditioning acc. to JEDEC Level 2

(nach J-STD-020C)

(acc. to J-STD-020C)



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¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.

EU RoHS and China RoHS compliant product



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